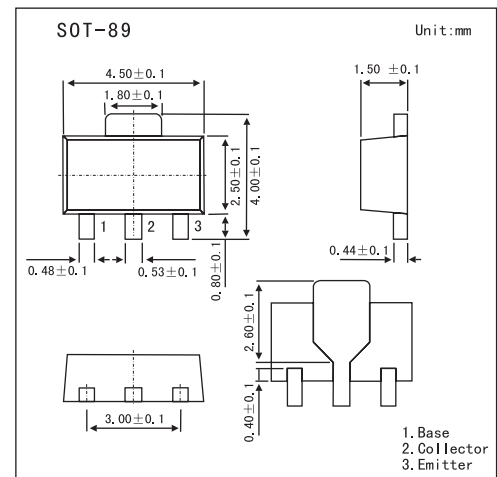


## NPN Epitaxial Silicon Transistor

## KSC2881

## ■ Features

- Collector-Emitter Voltage :  $V_{CE0}=120V$
- Current Gain Bandwidth Product :  $f_T=120MHz$
- Collector Dissipation :  $P_C=1$  to  $2W$  in Mounted on Ceramic Board

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	120	V
Collector-Emitter Voltage	$V_{CE0}$	120	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	800	mA
Base Current	$I_B$	160	mA
Collector Power Dissipation	$P_C$	500	mW
	$P_{C^*}$	1,000	mW
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to +150	$^\circ C$

\* Mounted on Ceramic Board (250mm<sup>2</sup>X0.8mm)

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$BV_{CE0}$	$I_C=10\mu A, I_B=0$	120			V
Emitter-Base Breakdown Voltage	$BV_{EB0}$	$I_E=1mA, I_C=0$	5			V
Collector Cut-off Current	$I_{CB0}$	$V_{CB}=120V, I_E=0$			100	nA
Emitter Cut-off Current	$I_{EB0}$	$V_{BE}=5V, I_C=0$			100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=100mA$	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=5V, I_C=500mA$			1.0	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=5V, I_C=100mA$		120		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$			30	pF

■  $h_{FE}$  Classification

Marking	SCO	SCY
Rank	O	Y
Type	80~160	120~240